In the Claims

Claim 1 (currently amended): A method of forming a plurality of capacitor devices, comprising:

forming conductive capacitor electrode material within openings in a first material mass, the first material mass comprising silicon and oxygen;

providing a retaining structure in physical contact with at least some of the conductive capacitor electrode material, the retaining structure comprising a dielectric material, the dielectric material of the retaining structure comprising silicon and nitrogen;

removing at least some of the first material mass while the retaining structure physically contacts the at least some of the conductive capacitor electrode material;

after removing at least some of the first material mass, incorporating the conductive capacitor electrode material into a plurality of capacitor devices; and

wherein the first material mass is over the retaining structure.

Claim 2 (canceled).

Claim 3 (previously presented): The method of claim 1 wherein the conductive capacitor electrode material is formed within the openings in the shape of upwardly-opening container structures.

Claim 4 (previously presented): The method of claim 1 wherein the conductive capacitor electrode material fills the openings to form conductive pedestals within the openings.

Claim 5 (currently amended): The method of claim 1 wherein the first material mass consists of one or more electrically insulative materials.

Claims 6 and 7 (canceled).

Claim 8 (currently amended): The method of claim 1 wherein the first material mass comprises one or more of borophosphosilicate glass, spin-on-glass, silicon dioxide, phosphosilicate glass, borosilicate glass, and silicon nitride.

Claim 9 (previously presented): The method of claim 1 wherein the retaining structure comprises silicon nitride.

Claim 10 (original): The method of claim 9 wherein the silicon nitride has a thickness of from about 50Å to about 3000Å.

Claim 11 (currently amended): The method of claim 1 wherein the first material mass comprises borophosphosilicate glass and the retaining structure comprises silicon nitride.

Claim 12 (previously presented): A method of forming a plurality of capacitor devices, comprising:

forming conductive capacitor electrode material within openings in a first material comprising silicon and oxygen;

providing a retaining structure in physical contact with at least some of the conductive capacitor electrode material;

removing at least some of the first material while the retaining structure physically contacts the at least some of the conductive capacitor electrode material;

after removing at least some of the first material, incorporating the conductive capacitor electrode material into a plurality of capacitor devices;

wherein:

the first material comprises borophosphosilicate glass;

a wet etch is utilized to remove at least some of the first material; and

the retaining structure comprises silicon nitride and a material having increased selectivity to borophosphosilicate glass than silicon nitride during the wet etch.

Claim 13 (original): The method of claim 12 wherein the material having increased selectivity to borophosphosilicate glass than silicon nitride during the wet etch consists essentially of silicon.

Claim 14 (original): The method of claim 12 wherein the material having increased selectivity to borophosphosilicate glass than silicon nitride during the wet etch includes polycrystalline silicon.

Claim 15 (original): The method of claim 14 wherein the polycrystalline silicon is over the silicon nitride.

Claim 16 (original): The method of claim 15 wherein the polycrystalline silicon has a thickness of from about 50Å to about 1000Å.

Claim 17 (original): The method of claim 15 wherein the polycrystalline silicon has a thickness of from about 50Å to about 1000Å; and wherein the silicon nitride has a thickness of from about 50Å to about 3000Å.

Claim 18 (original): The method of claim 14 wherein the polycrystalline silicon is under the silicon nitride.

Claim 19 (original): The method of claim 14 wherein the polycrystalline silicon is over and under the silicon nitride.

Claim 20 (original): The method of claim 19 wherein the polycrystalline silicon below the silicon nitride has a thickness of from about 50Å to about 500Å; wherein the polycrystalline silicon above the silicon nitride has a thickness of from about 50Å to about 500Å; and wherein the silicon nitride has a thickness of from about 50Å to about 1000Å.

Claim 21 (original): The method of claim 14 wherein the polycrystalline silicon entirely surrounds the silicon nitride.

Claims 22-91 (canceled).